

IN THE CLAIMS:

Claims 16 through 21 were previously cancelled. Claims 1 and 3 through 15 have been amended herein. All of the pending claims are presented below. This listing of claims will replace all prior versions and listings of claims in the application. Please enter these claims as amended.

Listing of Claims:

1. (Currently amended) A semiconductor processing assembly, comprising:
a reaction chamber configured to house at least one semiconductor substrate;
a heater located at least partially within said- the reaction chamber;
at least one temperature sensor configured to sense a temperature and transmit a signal in response to a sensed temperature; and
a temperature regulator in communication with said- the heater and said- the at least one temperature sensor and configured to continuously vary a thermal output of said- the heater and a temperature of at least a portion of said- the at least one semiconductor substrate responsive to said- the signal.
2. (Original) The semiconductor processing assembly of claim 1, comprising a plurality of temperature sensors for sensing temperatures at a corresponding plurality of locations.
3. (Currently amended) The semiconductor processing assembly of claim 1, wherein said- the at least one temperature sensor is configured to sense a temperature within said- the reaction chamber.

4. (Currently amended) The semiconductor processing assembly of claim 1, wherein
~~said-the~~ at least one temperature sensor is configured to sense a temperature of at least an area of
~~said-the~~ at least one semiconductor substrate.

5. (Currently amended) The semiconductor processing assembly of claim 1, wherein
~~said-the~~ temperature regulator is configured to vary ~~said-the~~ thermal output of ~~said-the~~ heater
over a span of time.

6. (Currently amended) The semiconductor processing assembly of claim 1, wherein
~~said-the~~ reaction chamber comprises at least one of a hot wall furnace and a cold wall furnace.

7. (Currently amended) The semiconductor processing assembly of claim 1, wherein
~~said-the~~ reaction chamber comprises at least one of a vertical furnace and a horizontal furnace.

8. (Currently amended) The semiconductor processing assembly of claim 1, wherein
~~said-the~~ reaction chamber is configured to house only a single semiconductor substrate at a time.

9. (Currently amended) The semiconductor processing assembly of claim 1, wherein
~~said-the~~ reaction chamber comprises a plasma enhanced chamber.

10. (Currently amended) The semiconductor processing assembly of claim 1, wherein
~~said-the~~ reaction chamber comprises at least one of a high-pressure chamber, a low-pressure
chamber, and an atmospheric-pressure chamber.

11. (Currently amended) The semiconductor processing assembly of claim 1, wherein
~~said-the~~ reaction chamber comprises at least one of a furnace and a rapid thermal processing
chamber.

12. (Currently amended) The semiconductor processing assembly of claim 1, further comprising a rotator within-said-the reaction chamber.

13. (Currently amended) The semiconductor processing assembly of claim 12, wherein-said-the rotator is configured to rotate-said-the at least one semiconductor substrate.

14. (Currently amended) A supplement to a fabrication chamber configured to perform a deposition process on a substrate,-said-the supplement comprising: a variable substrate temperature generation system configured to operate in cooperation with initiation of-said-the deposition process,-said-the variable substrate temperature generation system comprising a feedback control system in communication with at least one temperature sensor and a heating element of-said-the fabrication chamber,-said-the feedback control system configured to cause-said-the heating element of-said-the fabrication chamber to continuously alter a thermal output within-said-the fabrication chamber and a temperature of at least a portion of the substrate in response to transmission of a signal from-said-the at least one temperature sensor.

15. (Currently amended) The supplement of claim 14, wherein-said-the feedback control system is configured to receive-said-the signal and to alter power provided to-said-the heating element in response to-said-the signal.

16.-21. (Cancelled)